

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Amended) A bipolar transistor, comprising:
 - a first semiconductor region of a first conductivity type defining a collector region;
 - a second semiconductor region of a second conductivity type defining a base region;
 - a third semiconductor region of said first conductivity type defining a emitter region; and
 - a metal layer providing contacts to said base and emitter regions;wherein the transistor has a specific area resistance less than ~~about~~ $500\text{m}\Omega\text{mm}^2$;
and
wherein said metal layer has a thickness greater than $3\mu\text{m}$.
2. (Original) A bipolar transistor according to claim 1, wherein the metal layer has a thickness no less than $4\mu\text{m}$.
3. (Amended) A bipolar transistor according to ~~any preceding claim~~, claim 1 wherein the metal layer has a thickness no less than $6\mu\text{m}$.
4. (Amended) A bipolar transistor according to ~~any preceding claim~~, claim 1 wherein the emitter region defines a first surface, the base region extending to said surface in locations defined by apertures through emitter region, said metal layer overlying said first surface.
5. (Original) A bipolar transistor according to claim 4, wherein adjacent apertures are spaced less than $100\mu\text{m}$ from each other.
6. (Canceled)